

METHOD FOR CUTTING WAFER

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Inventor(s): YAMAOKA YOSHIFUMI

Applicant(s): HEWLETT PACKARD CO <HP>

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Abstract

PROBLEM TO BE SOLVED: To cut a gallium nitride group compound semiconductor wafer having a sapphire substrate to a chip shape with a conventionally used dicing saw in a simple process.

SOLUTION: Relating to a method for cutting a gallium nitride group compound semiconductor wafer 2, whose substrate is sapphire and its thickness is 50-450 μ m, to a chip shape with a dicing saw, a V shape rotary blade of tool angle 30 deg.-75 deg. is used as a blade 2 of the dicing saw, and after a lattice groove 3 is formed, by cutting, only on one surface of the wafer 2 with the dicing saw, the wafer 2 is press-split.

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